

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	599	(438/758).CCLS.	USPAT	OR	OFF	2005/05/11 10:57
L2	975	(438/592).CCLS.	USPAT	OR	OFF	2005/05/11 10:57
L3	855	(438/653).CCLS.	USPAT	OR	OFF	2005/05/11 10:58
L4	5975	polysilicon and doped and oxidized and mask	USPAT	OR	OFF	2005/05/11 10:58
L5	117	polysilicon and doped and (remove with oxidized) and mask	USPAT	OR	OFF	2005/05/11 10:58
L6	0	polysilicon and (pre-doped) and (remove with oxidized) and mask and antimoney	USPAT	OR	OFF	2005/05/11 10:58
L7	0	polysilicon and (pre-doped) and (remove with oxidized) and mask and antimony	USPAT	OR	OFF	2005/05/11 10:59
L8	0	polysilicon and (pre-doped) and (remove with oxidized) and mask and insulator	USPAT	OR	OFF	2005/05/11 10:59
S1	569	(438/758).CCLS.	USPAT	OR	OFF	2004/12/15 13:10
S2	73	S1 and polysilicon and gate	USPAT	OR	OFF	2004/12/15 13:10
S3	1	S1 and polysilicon and gate and wafer and dope	USPAT	OR	OFF	2004/12/15 13:10
S4	31	S1 and polysilicon and gate and wafer and nitrogen	USPAT	OR	OFF	2004/12/15 13:10
S5	5	S1 and polysilicon and gate and wafer and (nitrogen with doped)	USPAT	OR	OFF	2004/12/15 13:10
S6	3	S1 and polysilicon and gate and wafer and (nitrogen with doped) and mask	USPAT	OR	OFF	2004/12/15 13:11
S7	8	polysilicon and gate and wafer and (nitrogen with doped) and mask and RTO	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/15 13:45
S8	0	polysilicon and gate and wafer and (nitrogen with doped) and mask and RTO and (phosphoric adj acid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/15 13:45
S9	5	polysilicon and gate and wafer and (nitrogen with doped) and mask and RTO and wet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/15 15:32

S10	0	polysilicon and gate and wafer and (nitrogen with doped) and mask and RTO and PEOX	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/15 13:54
S11	2	polysilicon and gate and wafer and (nitrogen with doped) and mask and RTO and SiON	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/15 13:56
S12	3	(plasma-enhanced) and (polysilicon) and mask and (wet adj etch) and RTO and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/15 13:57
S13	3338	PEO	USPAT	OR	OFF	2004/12/15 15:32
S14	274	PEOX	USPAT	OR	OFF	2004/12/15 15:34
S15	33	PEOX and (plasma adj enhanced) and oxygen	USPAT	OR	OFF	2004/12/15 15:39
S16	1	("6456335").PN.	USPAT	OR	OFF	2005/05/10 16:18
S17	1	("6465335").PN.	USPAT	OR	OFF	2005/05/10 16:18